

22	5	((silicon and (doped or undoped)) and resistivity) and ceramic near2 Heat\$3) and range near2 order	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:12
23	74	((silicon and (doped or undoped)) and resistivity) and ceramic near2 Heat\$3) and range same order withtwo	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:12
24	0	((silicon and (doped or undoped)) and resistivity) and ceramic near2 Heat\$3) and range same order with two	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:12
25	1	((silicon and (doped or undoped)) and resistivity) and ceramic near2 Heat\$3) and range same order with five	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:14
26	0	(silicon and (doped or undoped)) and resistiv\$3 with oder	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:32
27	1	((silicon and (doped or undoped)) and resistivity) and range with oder	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:19
28	2056	(silicon and (doped or undoped)) and resistivity with range	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:32
29	1017	(silicon and (doped or undoped)) and resistivity near2 range	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:21
30	170	((silicon and (doped or undoped)) and resistivity near2 range) and (doped and undoped)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:22
31	0	((silicon and (doped or undoped)) and resistivity near2 range) and (doped and undoped)) and magnitude near2 five	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:22
32	29	((silicon and (doped or undoped)) and resistivity near2 range) and (doped and undoped)) and magnitude same range	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:23
33	2758	(silicon and (doped or undoped)) and resistiv\$3 with order	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:32
34	2278	(silicon and (doped or undoped)) and resistivity with order	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:33
35	1303	(silicon and (doped or undoped)) and heatinf adl element with resistivity with order	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:33
36	27816	(silicon and (doped or undoped)) and heating adl element with resistivity with order	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:33
37	1	(silicon and (doped or undoped)) and heating adj element with resistivity with order	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:34

	4	(silicon and (doped or undoped)) and heating adj element same resistivity with order	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:35
	0	(silicon and (doped or undoped)) and heating adj element same resistivity with comparison	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:35
40	7	(silicon and (doped or undoped)) and heating adj element same resistivity with compar\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:35
12	31	(nitrogen with ppm same ceramic) and resistivity	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:43
5	135	nitrogen with ppm same ceramic	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:45
8	452919	(nitrogen with ppm same ceramic) and doped near2j ceramic	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:46
18	201	((silicon and (doped or undoped)) and resistivity) and ceramic near2 Heat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:47
3	255	219/468.1	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:54
41	1	219/468.1 and (doped and undoped)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:55
42	6	219/468.1 and doped	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:57
43	6	219/468.1 and dop\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:57
19	73	((silicon and (doped or undoped)) and resistivity) and ceramic near2 Heat\$3) and magnitude	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/08 15:59